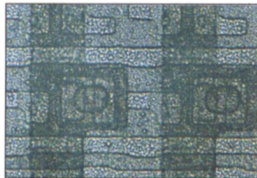
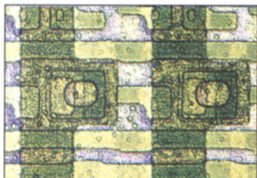


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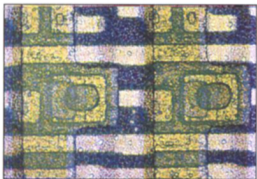
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E-MRS To Hold 1993 Spring Meeting in Strasbourg, May 4-7

The 1993 Spring Meeting of the European Materials Research Society (E-MRS), will be held May 4-7 at the Council of Europe and European Parliament in Strasbourg, France. The four-day program, which includes an equipment exhibit, will feature eight symposia covering such topics as semiconductor materials, deposition processes, micro- and optoelectronics, ion beam synthesis, and molecular electronics. Following are descriptions of each symposium; for further details, please contact the symposium chairs.

For general information on the conference, contact the E-MRS Secretary:

Paul Siffert, E-MRS 1993 Spring Meeting
BP 20, 67037 Strasbourg Cedex 2, France
Phone: 33-88-28-65-43
Fax: 33-88-28-62-93.

Symposium A: Semiconductor Materials for Optoelectronic Devices, OEICs, and Photonics

The four-day symposium will study semiconductor materials and heterostructures for single optoelectronic devices. The materials systems covered will be III/V, II/VI, IV/VI, lattice-matched and non-lattice-matched heterostructures.

Chairs: J-P. Hirtz, Thomson-CSF, France, phone 33-1-60-19-73-40, fax 33-1-60-19-78-29; C. Whitehouse, Defense Research Agency, United Kingdom, phone 44-684-89-5098, fax 44-684-89-5603; H.P. Meier, IBM Research Lab, Rüschlikon, Switzerland, phone 41-1-724-8358, fax 41-1-724-1789.

Symposium B: Low-Temperature Molecular Beam Epitaxial III-V Materials: Physics and Application

Main topics at this symposium will include growth and characterization of undoped high-resistive LTMBE III-V epitaxial layers (GaAs, InGaAs, InAlAs, and InP), application of LTMBE III-V layers in microelectronics (MESFETS, HEMTS, MISFETS, etc.), and optoelectronic applications of LTMBE GaAs.

Chairs: H.J. von Bardeleben, Universities of Paris 6 & 7, France, phone 33-1-44-27-79-48, fax 33-1-43-54-28-78; M.O. Manshah, Wright Patterson AFB, USA, phone (513) 255-4736, fax (513) 255-3374.

Symposium C: Ion Beam, Plasma, Laser, and Thermally Stimulated Deposition Processes

The three-and-a-half-day symposium will provide an overview of the current sta-

tus and trends in the deposition processing of films or coatings, stimulated by various means for performing compositional changes and surface modification of materials. Highlighted will be the properties of dielectric and optical coatings, hard and protective coatings, amorphous or polycrystalline silicon and semiconductor compounds, and advanced materials for ULSI metallization.

Chairs: J. Dieleman, DSA Consultants, The Netherlands, phone 31-4904-136-82, fax 31-4074-20-81; H. Freller, Siemens AG, Germany, phone 49-9131-7-21138, fax 49-9131-7-31806; Y. Pauleau, National Polytechnic Institute and Nuclear Research Center of Grenoble, France, phone 33-76-88-59-62, fax 33-76-88-51-30.

Symposium D: Integrated Processing for Micro- and Optoelectronics

Topics covered in this symposium are single and multichamber integrated processing, diagnostic and real-time control, process and tool modeling, and tool engineering.

Chairs: Y.I. Nissim, France Telecom, France, phone 33-1-42-31-73-19, fax 33-1-42-53-49-30; A. Katz, AT&T Bell Laboratories, USA, phone (908) 582-2261, fax (908) 582-4347; G.W. Rubloff, IBM Research, USA, phone (914) 945-1142, fax (914) 945-4201.

Symposium E: Light Emission from Silicon

This symposium will look at porous silicon properties, structure, and growth mechanisms; electro- and photoluminescence properties; light-emission mechanisms; other light-emitting silicon structures; the technology of light-emitting silicon; and applications.

Chairs: L.T. Canham, Defense Research Agency, United Kingdom, phone 44-684-89-50-07, fax 44-684-89-45-40; W. Lang, Fraunhofer-Institute for Solid State Technology, Germany, phone 49-89-5-47-59-226, fax 49-89-5-57-59-100; J-C. Vial, Joseph Fourier University, France, phone 33-76-51-58-66, fax 33-76-51-45-44.

Symposium F: Advances in Solidification Process

This three-day symposium offers numerical and analytical ways to describe solidification and crystallization, thermodynamics and kinetics during crystal growth and solidification, heat and mass flow due to convection and conduction

during solidification processes, the relationship between material properties and casting processes, the development of new processes, metastable solidification processes, cast metal matrix composites, and nonmetal solidification processing.

Chairs: H. Fredriksson, Royal Institute of Technology, Sweden, phone 46-8-790-78-69, fax 46-8-21-65-57; H. Jones, University of Sheffield, United Kingdom, phone 44-742-768-555, fax 44-742-754-325; G. Lesoult, School of Mines (Nancy), France, phone 33-83-57-42-38, fax 33-83-57-97-94.

Symposium G: Materials Aspects of Ion Beam Synthesis: Phase Formation and Modification

The symposium will provide a broad overview of the current status of high-dose ion implantation used for phase synthesis and modification, and will cover the science and technology of compound formation and phase modification by ion beam synthesis, with the aim of expanding the discussion of this rapidly developing technology into new areas.

Chairs: P.L.F. Hemment, University of Surrey, United Kingdom, phone 44-483-

509144, fax 44-483-34139; J.A. Kilner, Imperial College, United Kingdom, phone 44-71-225-8701, fax 44-71-584-3194.

Symposium H: Molecular Electronics: Doping and Recognition in Nanostructured Materials

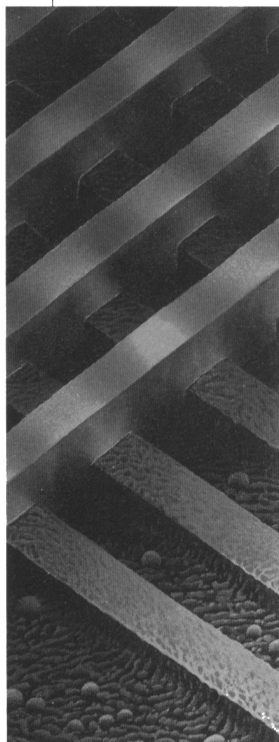
This two-and-a-half-day symposium will bring together basic science and application-oriented scientists who have a special interest in the controlled synthesis and engineering of organic materials. Emphasis will be on the reproducible synthesis of clean materials, the characterization of intrinsic properties, and controlled (irreversible) doping or (reversible) sensor effects. Polymers, oligomers, molecular crystals, and supramolecular structures will be discussed.

Chairs: W. Göpel, University of Tübingen, Germany, phone 49-7071-296904, fax 49-7071-296910; G. Zerbi, Milan Polytechnique, Italy, phone 39-2-239-93235, fax 39-2-239-93231.

Proceedings of the E-MRS 1993 Spring Meeting will be published by Elsevier Science Publishers, North Holland. □

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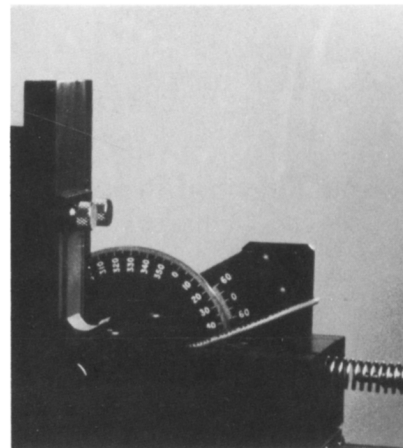
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